

Chemical Sputtering of Carbon Materials due to Combined Bombardment by Ions and Atomic Hydrogen

<u>Wolfgang Jacob</u>, C. Hopf, M. Schlüter, and T. Schwarz-Selinger Max-Planck-Institut für Plasmaphysik, 85748 Garching, Germany

Content:

- Physical sputtering, chemical erosion, and chemical sputtering
- The MAJESTIX experiment
- Chemical Sputtering: Initial experimental results (Ar⁺)
- Quantitative model energy dependence
- New experimental results for Ne⁺, He⁺, and N₂⁺
- Summary

Chemical vs. physical sputtering





Physical sputtering

- threshold energy
- energy dependence (TRIM.SP)
- isotope effect (kinematic factor)
- no significant T
 dependence
- all species (incl. inert gases)

Chemical sputtering

- •ions + neutrals
- energy dependence
- T dependence
- very low threshold energy
- isotope effect
- ion-to-neutral ratio dep.
- high erosion yield

Chemical erosion

- thermally activated (no threshold energy)
- no isotope effect
- requires chemically reactive species

Experimental set-up



UHV experiment with 2 radical beam sources and one ion beam source



Ion | H synergism Chemical Sputtering



Christian Hopf, PhD Thesis

Ch. Hopf, A. von Keudell, and W. Jacob, "Chemical Sputtering of Hydrocarbon Films by Low-energy Ar⁺ Ions and H Atom Impact", Nuclear Fusion **42**, L27 (2002). Ch. Hopf, A. von Keudell, and W. Jacob, "Chemical Sputtering of Hydrocarbon Films", J. Appl. Phys. **94**, 2373 (2003).

Erosion of a-C:H layers

Ņ

comparison of simple physical sputtering (blue symbols) due to Ar ions with

erosion due to simultaneous interaction of H and Ar⁺ (green symbols).

- enhanced erosion above 200 eV for simultaneous interaction
- erosion below threshold for physical sputtering (threshold energy for physical sputtering ≈ 60 eV
- erosion at 20 eV >> pure chemical erosion ⇒ '*chemical sputtering*'
- separation of chemical and kinematical effects due to use of Ar⁺ and H
- neutral / ion ratio ≈ 400



Ar⁺|H flux dependence





$$Y_{\text{Modell}} = Y_{\text{phys}}(1 - \Theta_{\text{CH}}) + Y_{\text{chem}}\Theta_{\text{CH}}$$

$$n_0 \frac{d\Theta_{\text{CH}}}{dt} = j_{\text{H}}(1 - \Theta_{\text{CH}})p_{\text{Einbau}}^{\text{H}} - j_{\text{Ion}}\Theta_{\text{CH}}p_{\text{Freisetzung}}^{\text{H}}$$

$$\text{Mit } R = j_{\text{H}}/j_{\text{Ion}} \text{ und } S = p_{\text{Freisetzung}}^{\text{H}}/p_{\text{Einbau}}^{\text{H}}$$

$$Y_{\text{Modell}} = Y_{\text{phys}} + \frac{R}{R+S}(Y_{\text{chem}} - Y_{\text{phys}})$$

$$\text{Fit parameters:}$$

$$S = 176$$

$$Y_{\text{chem}} = 2.86$$

 $Y_{phys} = 0.12$

Ar⁺|H flux dependence





Saturation requires much more H than ions (R > 1000)

Chemical sputtering mechanism





PSIF Workshop, OakRidge © Wolfgang Jacob, March 2005

Energy dependence





Energy dependence





 j_{H} = 1.4×10¹⁵ cm⁻² s⁻¹, j_{Ar+} = 3.6×10¹² cm⁻² s⁻¹, R = $j_{H/}j_{Ar} \approx 400$









 Good fit of the energy dependence, but only for a = 0.6 (instead of 0.4)

Chemical sputtering by N₂⁺





- TRIM cannot describe the results for pure N₂⁺
- yield \geq 1 for E_{ion} > 50 eV
- Threshold between 20 and 50 eV (TRIM ca. 100 eV)
- almost no energy dependence in range 50 to 900 eV

Chemical sputtering: $N_2^+ + H$



IPP

- Good fit of the energy dependence, but only for a = 0.6 (instead of 0.4)
 - yield \geq 1 in whole range
 - highest chem. Sputt. yield of all investigates species (good mass match to C, two atoms per ion, chemical activity)

Chemical sputtering: Summary





PSIF Workshop, OakRidge © Wolfgang Jacob, March 2005

Energy dependence: Modeling results





Chemical sputtering with reactive ions





New weight-loss measurements of the chemical erosion yields of carbon materials under hydrogen ion bombardment

IPP

total yield	=	chemical sputtering	+	physical sputtering
Y(E)	=	$\int y_{bb}^{C}(x,E) n(x,E) \exp(-x/\lambda) dx$	+	$Y_{\rm phys}(E)$

$Y_{\rm phys}(E)$	phys. sputtering yield	TRIM.SP	
$y_{bb}^{C}(x,E)$	ion induced damage	$E_{\rm sb}^{\rm C} = 7.4 {\rm eV}$	
n(x,E)	implanted hydrogen	E_{bb}^{30} C = 5.0 eV	
exp(–x/λ)	depth dependent probability for outdiffusion of erosion products	λ = 0.4 nm	



particle-beam experiments

- chemical sputtering: increase of yield and lowering of threshold
- mechanistic model for chemical sputtering
- flux dependence (rate equation model): high H fluxes required
- energy dependence: bond breaking × passivation
- data for Ar, Ne, He, and N₂
- predictions for other ions, e.g. H, D, and T
- N₂⁺ alone results in *chemical sputtering* of a-C:H layers
- N₂⁺ + H shows very high *chemical sputtering* yield

The end

Collaborators:

Christian Hopf Achim von Keudell Michael Schlüter Thomas Schwarz-Selinger